

Characterization of Ge nanocrystals embedded in SiO₂b

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Synthesis and Raman Spectroscopy of Nanoparticles of Crystalline and X-ray Amorphous Germanium within Mesoporous SiO ₂ . Zeitschrift Fur Anorganische Und Allgemeine Chemie, 2004, 630, 864-868.	0.6	11
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4	Synthesis of crystalline Ge nanoclusters in PE-CVD-deposited SiO ₂ films. Applied Physics A: Materials Science and Processing, 2005, 81, 1591-1593.	1.1	3
5	Can chemically etched germanium or germanium nanocrystals emit visible photoluminescence?. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1472-1476.	0.8	21
6	Preparation of Room-Temperature Photoluminescent Nanoparticles by Ultrafast Laser Processing of Single-Crystalline Ge. Japanese Journal of Applied Physics, 2005, 44, 5278-5281.	0.8	13
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11	Formation of Si and Ge quantum structures by laser-induced etching. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2444-2450.	0.8	27
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14	Ion beam synthesis and characterization of Ge nanoparticles in SiO ₂ . Nuclear Instruments & Methods in Physics Research B, 2006, 249, 843-846.	0.6	11
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19	Structural properties of Ge nanocrystals embedded in sapphire. <i>Journal of Applied Physics</i> , 2006, 100, 114317.	1.1	22
20	Charge retention and optical properties of Ge nanocrystals embedded in GeO ₂ matrix. <i>Solid State Communications</i> , 2007, 143, 213-216.	0.9	30
21	Raman and TEM studies of Ge nanocrystal formation in SiO _x :Ge/SiO _x multilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 288-291.	0.8	6
22	Formation, Dynamics, and Characterization of Nanostructures by Ion Beam Irradiation. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2007, 32, 1-50.	6.8	71
23	Complementary application of Raman scattering and GISAXS in characterization of embedded semiconductor QDs. <i>Superlattices and Microstructures</i> , 2008, 44, 385-394.	1.4	0
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40	Structural, mechanical and optical properties of Ge nanocrystals embedded in superlattices fabricated by in situ low temperature annealing. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012, 45, 207-213.	1.3	2
41	Laser produced streams of Ge ions accelerated and optimized in the electric fields for implantation into SiO ₂ substrates. <i>Review of Scientific Instruments</i> , 2012, 83, 02B305.	0.6	2
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52	Silicon and silicon-germanium nanoparticles obtained by Pulsed Laser Deposition. <i>Applied Surface Science</i> , 2019, 466, 375-380.	3.1	9
53	XTEM study of low-energy ion-beam synthesized Ge nanoclusters inside SiO _x matrix. <i>Bulletin of Materials Science</i> , 2021, 44, 1.	0.8	0
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55	Ge nanoparticles based MOS structure and their Raman characterization. <i>EPJ Applied Physics</i> , 2007, 38, 27-30.	0.3	2
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